

**ABSTRACT**

A semiconductor device includes an insulation film 6 formed on a silicon substrate 1, a buried metal interconnect 8 formed in the insulation film 6, and a barrier metal film 7 formed between the insulation film 6 and the metal interconnect 8. The barrier metal film 7 is a metal compound film. The metal compound film is characterized by including at least one of elements forming the insulation film.